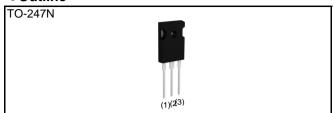


N-channel SiC power MOSFET

V _{DSS}	750V
R _{DS(on)} (Typ.)	13mΩ
I _D ^{*1}	105A
P_{D}	312W

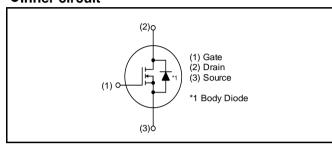
Outline



Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

●Inner circuit



Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Type	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT4013DE

● **Absolute maximum ratings** (T_{vj} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	750	V	
Continuous drain ,	\/ _\/	$T_c = 25^{\circ}C$, , *1	105	А
and source current	$V_{GS} = V_{GS_on}$	T _c = 100°C	Ι _D , Ι _S *1	74	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	T _c = 25°C	I _{D,pulse} *2	233	А
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I _{S,pulse} *1,*3	105	Α
Body diode surge forward current $V_{GS} = 0$		$V_{GS} = 0 V$	I _{S,pulse} *1,*4	233	А
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V	
Gate - source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	${\sf V_{GS_on}}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V	
Virtual junction temperature		T_{vj}	175	°C	
Range of storage temper	erature		T_{stg}	-40 to +175	°C

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol Conditions -		Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown	W	$V_{GS} = 0 \text{ V}, I_D = 18.6\text{mA}$				V
voltage	V (BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V , V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 30.8 \text{mA}$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 58A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	13.0	16.9	mΩ
5 5		T _{vj} = 150°C	-	22.2	-	
Gate input resistance	R_{G}	f = 1MHz, open drain		1	-	Ω

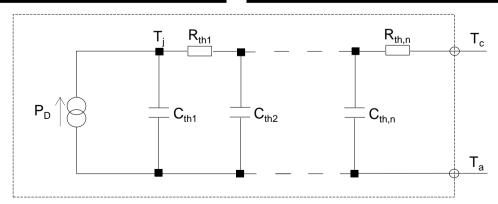
●Thermal resistance

Parameter	Symbol	Values			Unit
Falametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC} *9	-	0.37	0.48	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	4.0 ×10 ⁻²	
R _{th2}	1.6 ×10 ⁻¹	K/W
R _{th3}	1.7 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	1.2 ×10 ⁻³	
C_{th2}	4.6 × 10 ⁻³	Ws/K
C _{th3}	2.6 ×10 ⁻²	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

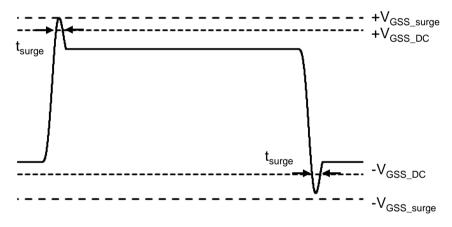
Doromotor	Cymphol	bol Conditions -	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g_{fs}^{*8}	$V_{DS} = 10V, I_{D} = 58A$	-	32	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	4580	-	
Output capacitance	C _{oss}	V _{DS} = 500V	1	203	ı	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	10	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	1	263	ı	pF
Total Gate charge	Q _g *8	$V_{DS} = 500V$ $I_{D} = 58A$	1	170	ı	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	1	39	ı	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	1	42	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 500V$ $I_{D} = 58A$	1	20	ı	
Rise time	t _r *8	$V_{GS} = +18V / 0V$	ı	57	ı	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 6.8\Omega$, L = 250µH E_{on} includes diode	ı	83	ı	113
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	21	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	1100	-	11.1
Turn - off switching loss	E _{off} *8		-	630	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Darameter	Cumbal	mbol Conditions -	Values			l lm:t
Parameter	Symbol		Min.	Тур.	Max.	Unit
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{S} = 58A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 58A$ $V_R = 500V$	ı	47	ı	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 1700A/µs	ı	420	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	18	-	А

^{*1} Limited by maximum T_{vj} and for Max. R_{thJC} .

*5 Example of acceptable V_{GS} waveform



- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

^{*2} Pulse width and duty cycle are limited by $T_{v_j,max}$.

^{*3} Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW \leq 10 μ s

Fig.1 Power Dissipation Derating Curve

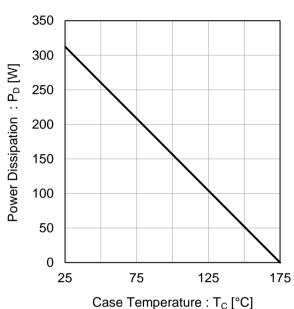


Fig.2 Maximum Safe Operating Area

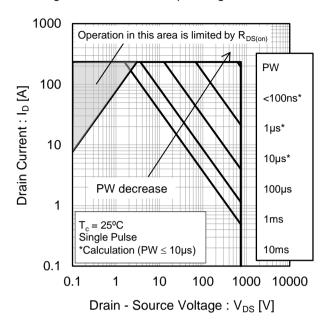
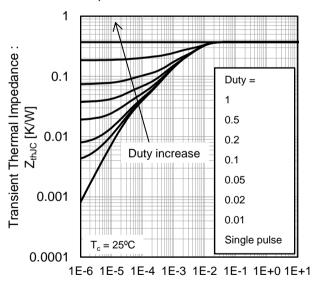
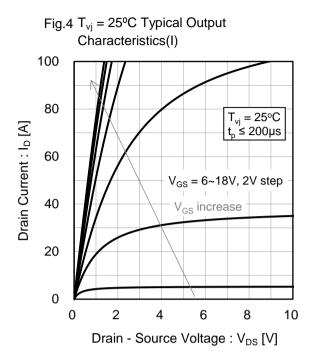


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



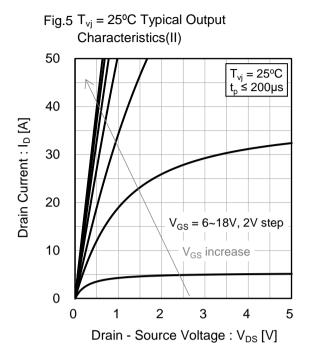
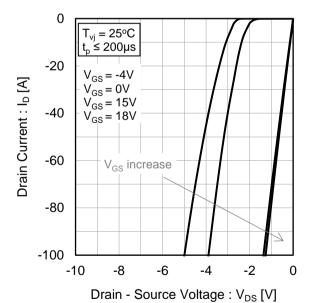
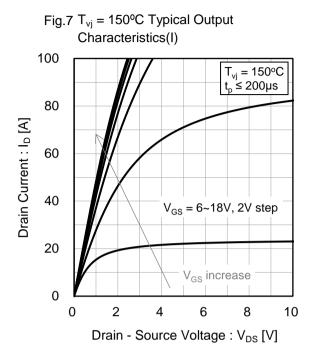
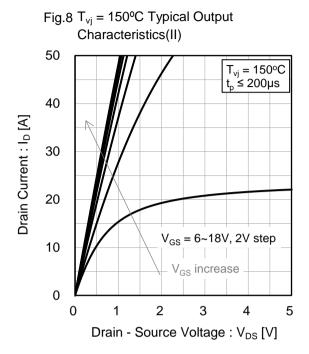
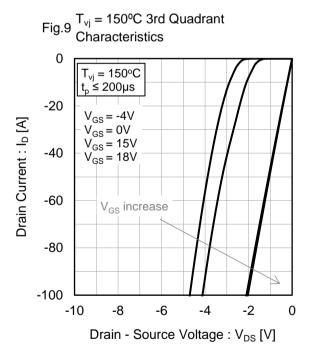


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics









vs. Gate - Source Voltage 6 Body Diode Forward Voltage: V_{SD} [V] $I_{D} = 58A$ t_p ≤ 200µs 5 4 3 T_{vi}=150°C 2 T_{vi}=25°C 1 0 0 8 12 16 20 Gate - Source Voltage : V_{GS} [V]

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Fig.10 Body Diode Forward Voltage

Fig.11 Typical Transfer Characteristics (I)

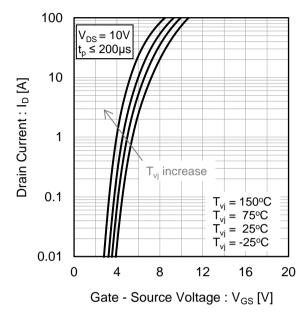


Fig.12 Typical Transfer Characteristics (II)

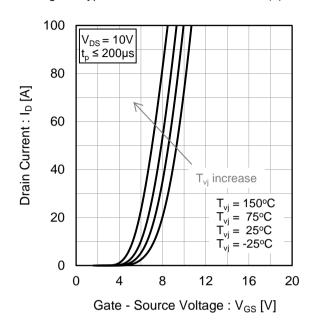


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

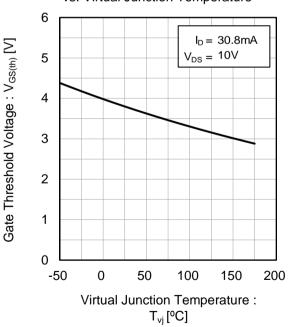
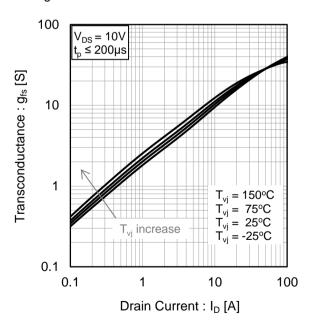
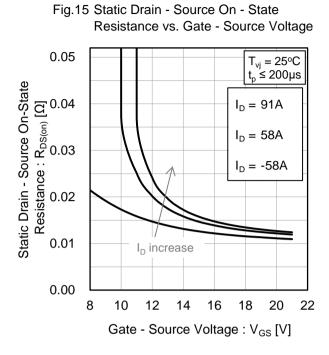


Fig.14 Transconductance vs. Drain Current

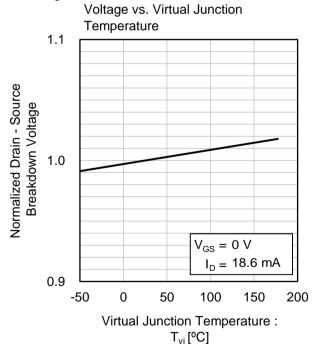




Resistance vs. Virtual Junction Temperature 0.05 $V_{GS} = 18V$ $t_p \le 200 \mu s$ Static Drain - Source On-State I_D = 91A = 58A $I_{D} = -58A$ 0.01 I_D increase 0.00 -50 0 50 100 150 200 Virtual Junction Temperature: T_{vi} [°C]

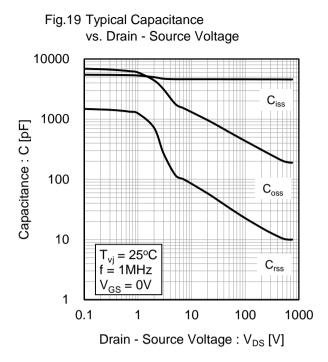
Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current = 150°C $T_{vi} = 125^{\circ}C$ Static Drain - Source On-State $T_{vj} = 75^{\circ}C$ = 25°C Resistance: R_{DS(on)} [Ω] = -25°C 0.1 0.01 T_{vj} increase $V_{GS} = 18V$ $t_p \le 200 \mu s$ 0.001 10 100 Drain Current: I_D [A]



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Fig.18 Normalized Drain - Source Breakdown



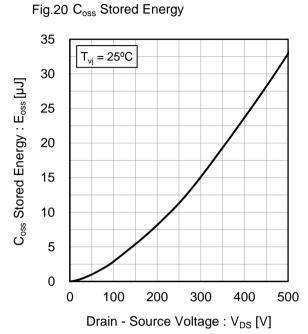


Fig.21 Dynamic Input Characteristics

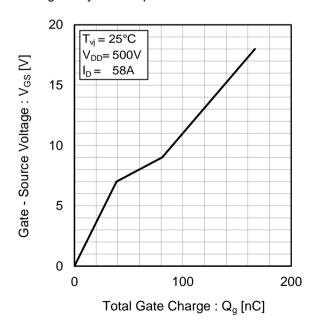


Fig.22 Typical Switching Time vs. External Gate Resistance

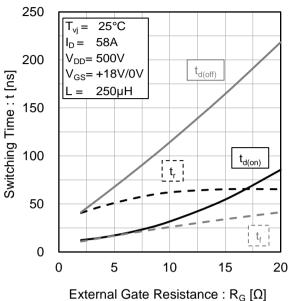


Fig.23 Typical Switching Loss vs. Drain - Source Voltage

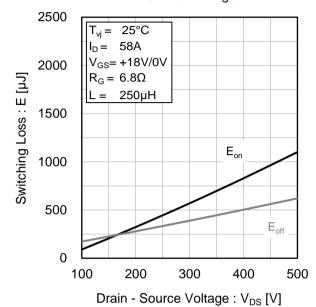


Fig.24 Typical Switching Loss vs. Drain Current

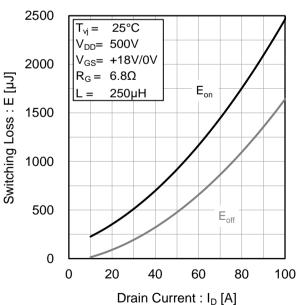
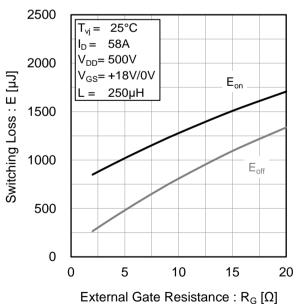


Fig.25 Typical Switching Loss vs. External Gate Resistance



Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

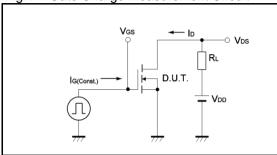


Fig.2-1 Switching Characteristics Measurement Circuit

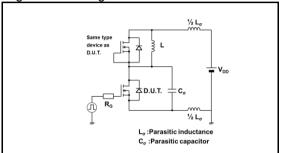


Fig.2-3 Waveforms for Switching Energy Loss

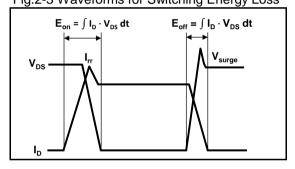


Fig.3-1 Reverse Recovery Time Measurement Circuit

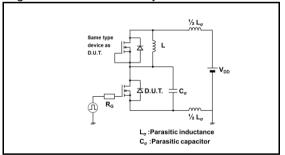


Fig.1-2 Gate Charge Waveform

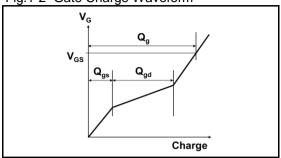


Fig.2-2 Waveforms for Switching Time

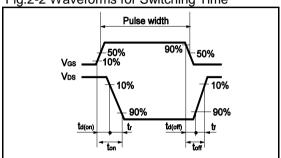
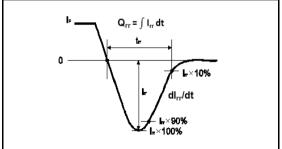
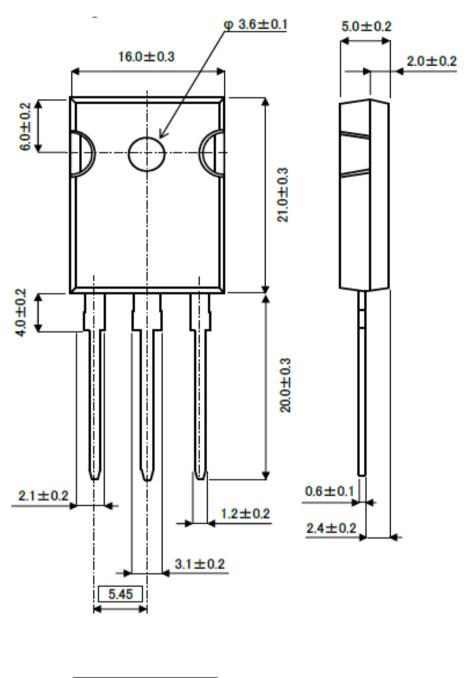


Fig.3-2 Reverse Recovery Waveform



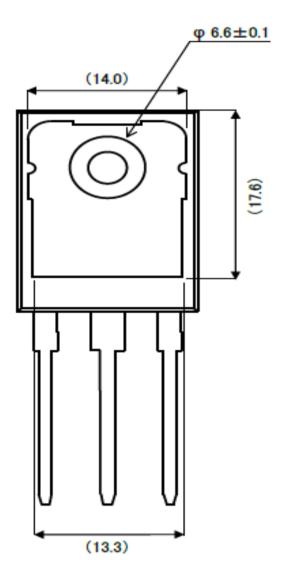
●Package Dimensions





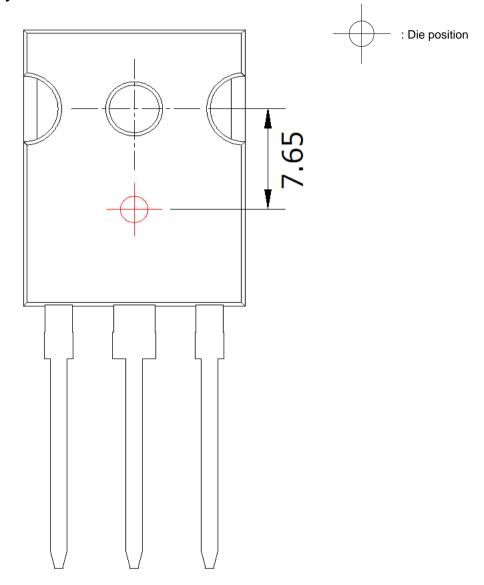
Unit: mm

Datasheet



Unit: mm

●Die Bonding Layout



- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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